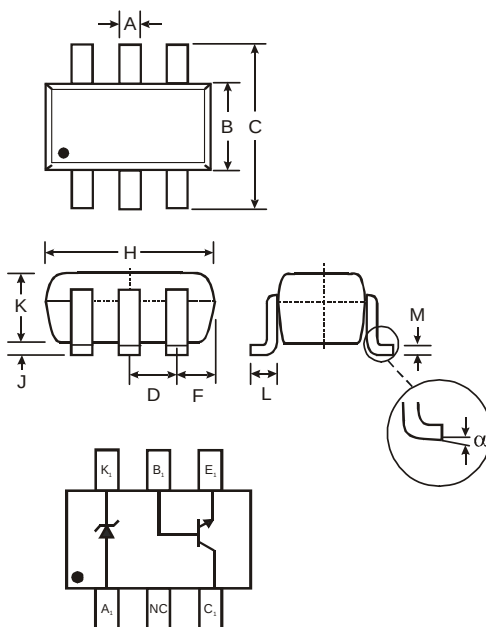


Features

- Epitaxial Planar Die Construction
- Selectively Paired NPN Transistors & Zener Diodes for Series Pass Voltage Regulator Circuits
- Ideally Suited for Automated Assembly Processes
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.008 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	8°	
All Dimensions in mm		

Maximum Ratings, Total Device

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	625	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, NPN Transistor

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	45	V
Collector-Emitter Voltage	V _{CEO}	18	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous (Note 3)	I _C	1	A

Maximum Ratings, Zener Element

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ I _F = 10mA	V _F	0.9	V

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics, NPN Transistor @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	45	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	18	—	V	I _C = 1mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	1	μA	V _{CB} = 40V, I _E = 0
Emitter Cutoff Current	I _{EBO}	—	1	μA	V _{EB} = 4V, I _C = 0
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	150	800	—	I _C = 100mA, V _{CE} = 1V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.5	V	I _C = 300mA, I _B = 30mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Current Gain-Bandwidth Product	f _T	100	—	MHz	V _{CB} = 10V, I _E = 50mA, f = 100MHz

Electrical Characteristics, Zener Element @T_A = 25°C unless otherwise specified

Type Number	Zener Voltage Range (Note 5)				Maximum Reverse Leakage Current	
	V _Z @ I _{ZT}			I _{ZT}	I _R @ V _R	
	Nom (V)	Min (V)	Max (V)	mA	μA	V
DVR1V8W	3.3	3.1	3.5	5	5	1
DVR2V5W	3.9	3.7	4.1	5	3	1
DVR3V3W	4.7	4.4	5.0	5	3	2
DVR5V0W	5.1	4.85	5.36	0.05	5	3

- Notes:
- Short duration test pulse used to minimize self-heating effect.
 - Nominal Zener voltage is measured with the device junction in thermal equilibrium at T_J = 30°C ±1°C.

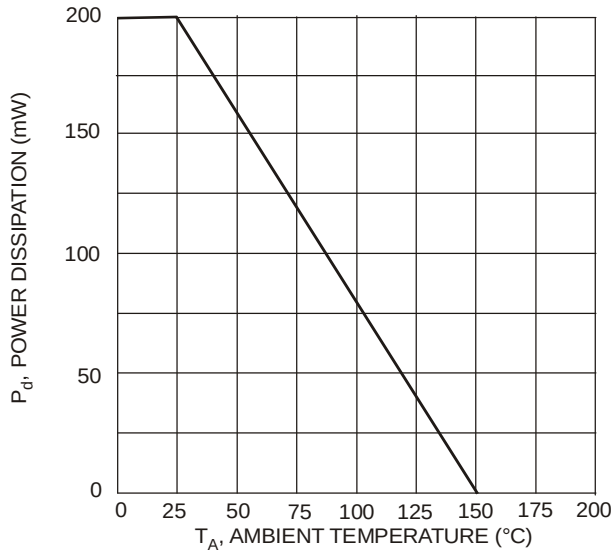


Fig. 1 Max Power Dissipation vs. Ambient Temperature (Total Device)

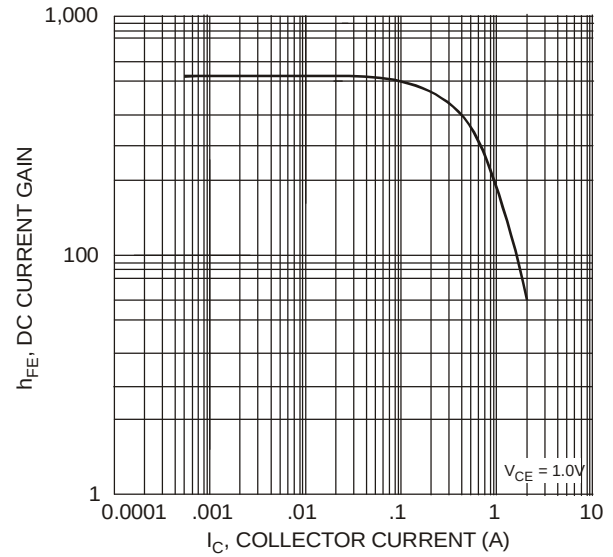


Fig. 2 Typical DC Current Gain vs. Collector Current (NPN Transistor)

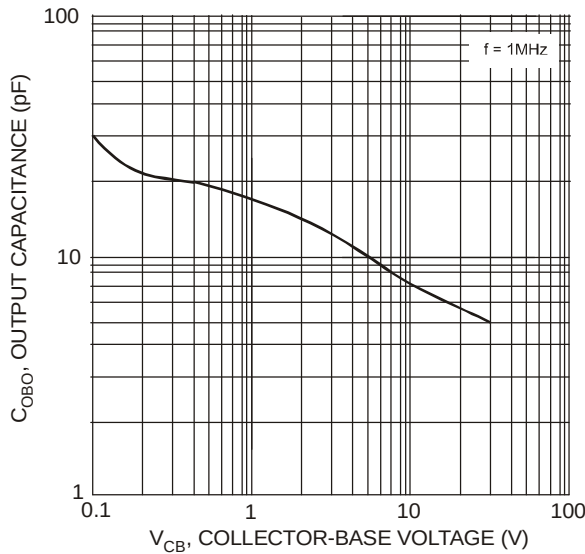


Fig. 3 Output Capacitance vs. Collector-Base Voltage (NPN Transistor)

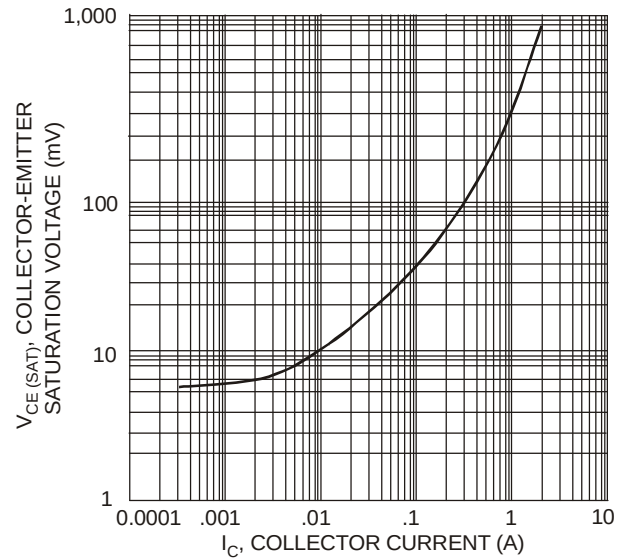


Fig. 4 Collector Saturation Voltage vs. Collector Current (NPN Transistor)

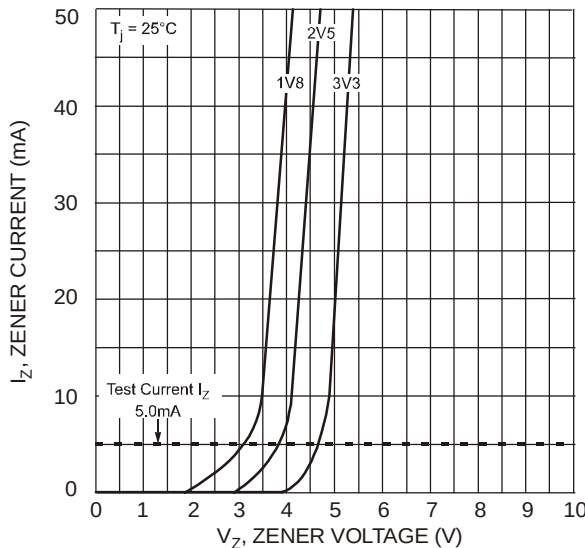


Fig. 5 Zener Breakdown Characteristics (DVR1V8W - DVR3V3W)

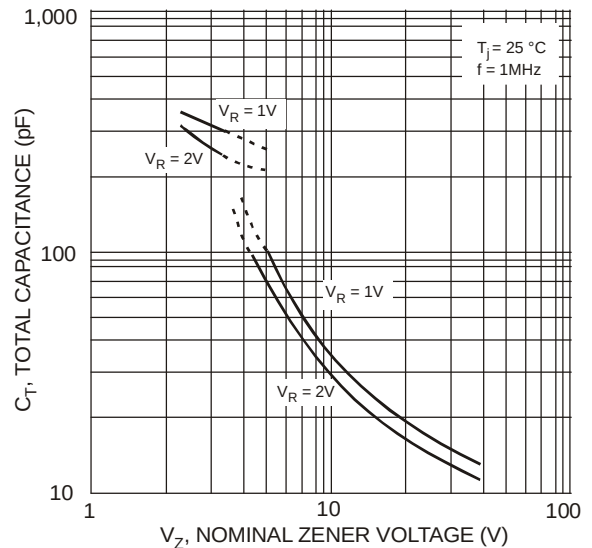


Fig. 6 Total Capacitance vs. Nominal Zener Voltage (DVR1V8W - DVR3V3W)

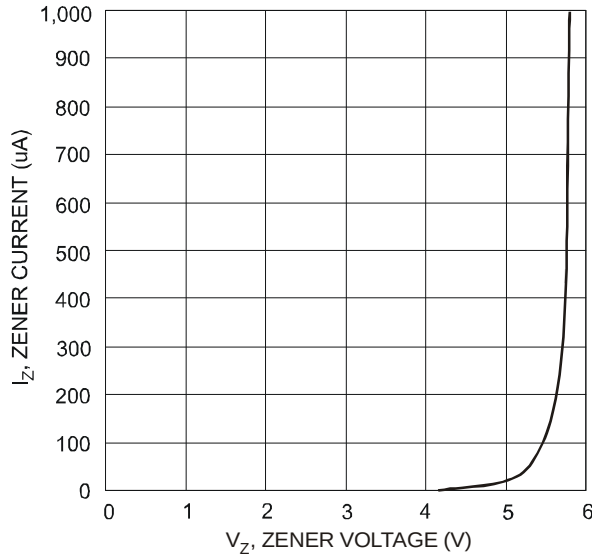


Fig. 7 Zener Breakdown Characteristics (DVR5V0W)

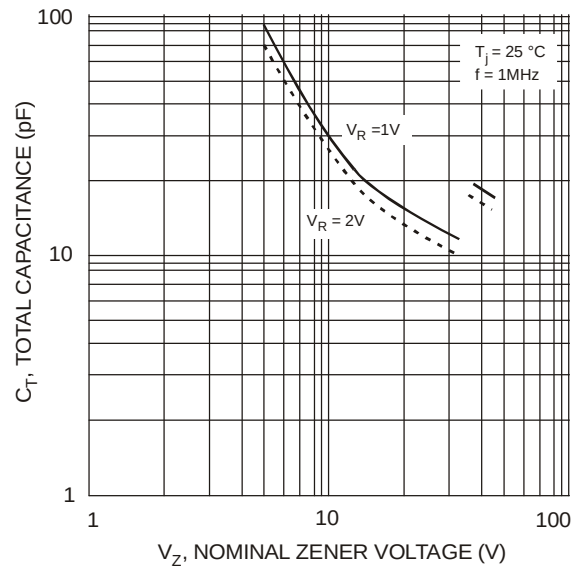


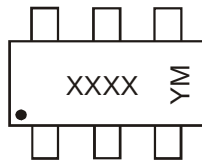
Fig. 8 Total Capacitance vs. Nominal Zener Voltage (DVR5V0W)

Ordering Information (Note 6)

Device	Packaging	Shipping
DVR1V8W-7	SOT-363	3000/Tape & Reel
DVR2V5W-7	SOT-363	3000/Tape & Reel
DVR3V3W-7	SOT-363	3000/Tape & Reel
DVR5V0W-7	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



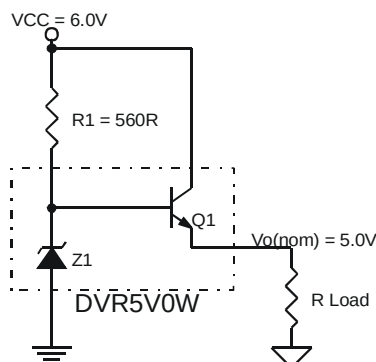
XXXX = Product Type Marking Code,
See Table Above, e.g., VR01 = DVR1V8W
YM = Date Code Marking
Y = Year ex: R = 2004
M = Month ex: 9 = September

Date Code Key

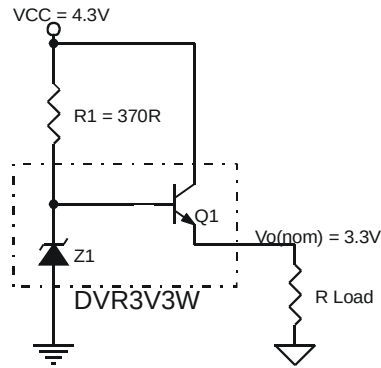
Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

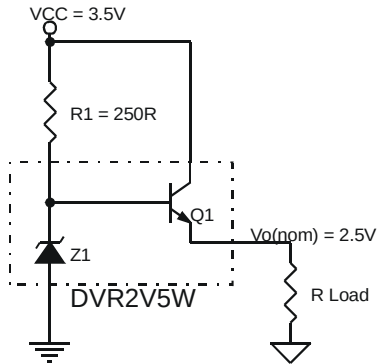
Sample Applications



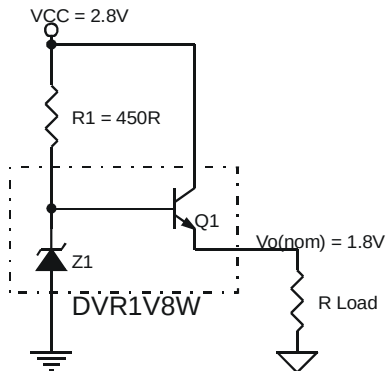
Sample Application for DVR5V0W:
 $V_{CC} = 6.0V$ $R1 = 560\Omega$
 $V_o(nom) = 5.0V$ $I_o = 100mA$
 $I_q(\text{typical}) = 0.5mA$ @ $I_o = 0mA$
 Typical $V_{reg}(load) = 0.2V$ from $I_o = 100mA$ to $0mA$



Sample Application for DVR3V3W:
 $VCC^9 = 4.3V$ $R1^7 = 370\Omega$
 $Vo(nom) = 3.3V$ $I_o = 100mA$
 $I_q(\text{typical}^8) = 0.7mA @ I_o = 0mA$
 $\text{Typical}^8 V_{reg}(\text{load}) = 0.21V \text{ from } I_o = 100mA \text{ to } 0mA$



Sample Application for DVR2V5W:
 $VCC^9 = 3.5V$ $R1^7 = 250\Omega$
 $Vo(nom) = 2.5V$ $I_o = 100mA$
 $I_q(\text{typical}^8) = 0.91mA @ I_o = 0mA$
 $\text{Typical}^8 V_{reg}(\text{load}) = 0.13V \text{ from } I_o = 100mA \text{ to } 0mA$



Sample Application for DVR1V8W:
 $VCC^9 = 2.8V$ $R1^7 = 450\Omega$
 $Vo(nom) = 1.8V$ $I_o = 100mA$
 $I_q(\text{typical}^8) = 0.55mA @ I_o = 0mA$
 $\text{Typical}^8 V_{reg}(\text{load}) = 0.25V \text{ from } I_o = 100mA \text{ to } 0mA$

- Notes:
7. Resistor R1 not included.
 8. Typical performance shown is under setup and operating conditions specified in the sample applications.
 9. Recommended $VCC(\text{min}) \sim Vo(\text{nom}) + 1V$.

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